Amendments to the Specification

Page 14, please delete the paragraph at lines 3-16, and substitute therefor the following new paragraph:

--Figure 2 represents supply of gas into the vacuum container 104, and operations of the magnetron 101 and rf bias power supply 109 during etching treatment by the system given in Figure 1. Illustratively, the rf bias voltage can have a frequency ranging from 200 kHz to 20MHz. Concurrently as gas is supplied and etching is started, gas pressure is kept constant, as shown in (a). Microwaves power is continuously supplied as shown in (b). Meanwhile, rf bias applied to the sample is subjected to periodic on-off control, as shown in (c). A high energy area and a low energy area are produced during the sample surface treatment by setting an ion acceleration on-off period through the on-off control of rf bias. In the low energy ion area, residual reaction product deposits in gas or plasma without etching in progress, as shown in (d). –

Please delete the paragraph from page 25, line 14 through page 25, line 2, and substitute therefor the following new paragraph:

--Figure 7 shows the temporal change of the etching profile of the sample during continuous application of radio frequency voltage (power 35W) according to the conventional method. A difference in etching depth 306 occurs between the p- and n- type silicons due to the difference of etching rate. This causes processing of n-type polycrystalline silicon 302 to be completed first, as shown in Figure 7 (c). Since etching residues remains in

the p-type silicon, a continued etching operation will cause oxide film missing area 310 to occur on the n-side when processing of p-type polycrystalline silicon 303 has completed, as shown in Figure ~~3-(d)~~7(d). A side etch 312 will also occur on the n-type polycrystalline silicon. Under this condition, a device failure will result, so some improvement must be made. –